

Table S1. The change in the mass of 3DG samples before and after the GQD deposition for 10 h.

Sample ID	Mass before	Mass after	Percentage of change
	GQDs deposition (g)	GQDs deposited (g)	in mass (%)
Sample 1	0.9635	0.9869	2.428
Sample 2	0.8973	0.9342	4.112
Sample 3	0.8903	0.9348	4.998
Sample 4	1.0737	1.0895	1.471
Sample 5	2.1018	2.1859	4.001
Sample 6	1.9715	1.9999	1.440

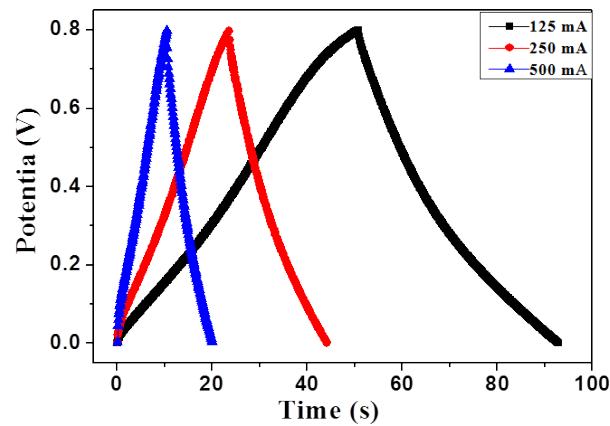


Fig. S1. Galvanostatic charge-discharge curves at a current density of 1.25 A g^{-1} , 2.5 A g^{-1} and 5 A g^{-1} for Devices D. Device D was assembled in the same configuration as Devices A, B and C except that it was fabricated from two 3DG electrodes that were applied a bias of 2 V for 10 h in the *GQD-free* solution. The calculated capacitance from the charge-discharge curve is 131 F g^{-1} at discharge current density of 1.25 A g^{-1} , nearly equal to the device A (3DG).